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FDC638P

P-Channel 2.5V PowerTrench® Specified MOSFET

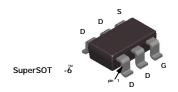
General Description

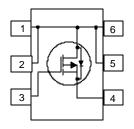
This PChannel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance

These devices are well suited for battery power applications: load switching and power management, battery charging circuits, and DC/DC conversion.

Features

- -4.5 A, -20 V. $R_{DS(ON)} = 48$ m Ω @ $V_{GS} = -4.5$ V $R_{DS(ON)} = 65$ m Ω @ $V_{GS} = -2.5$ V
- Low gate charge (10 nC typical)
- High performance trench technology for extremely low R_{DS(ON)}
- SuperSOT [™] –6 package: small footprint (72% smaller than standard SO-8; low profile (1mm thick)





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	-4.5	А
	- Pulsed		-20	
P _D	Power Dissipation for Single Operation	(Note 1a)	1.6	w
		(Note 1b)	0.8	vv
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
.638	FDC638P	7"	8mm	3000 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			I	ı	I
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to 25°C		-14		mV/°C
loss	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)			•		•
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-0.8	-1.5	V
ΔV _{GS(th)} ΔT _J	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μA,Referenced to 25°C		3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$\begin{aligned} &V_{GS} = -4.5 \text{ V}, & I_D = -4.5 \text{ A} \\ &V_{GS} = -2.5 \text{ V}, & I_D = -3.8 \text{ A} \\ &V_{GS} = -4.5 \text{ V}, I_D = -4.5 \text{ T}_J = 125 ^{\circ}\text{C} \end{aligned}$		39 52 54	48 65 72	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-20			Α
G FS	Forward Transconductance	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -4.5 \text{ A}$		15		S
Dynamic	: Characteristics			•		•
Ciss	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$		1160		pF
Coss	Output Capacitance	f = 1.0 MHz		195		pF
C _{rss}	Reverse Transfer Capacitance	1		105		pF
Switchin	g Characteristics (Note 2)			•		•
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -5 \text{ V}, \qquad I_D = -1 \text{ A},$		12	22	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		9	18	ns
t _{d(off)}	Turn-Off Delay Time	1		33	53	ns
t _f	Turn-Off Fall Time	1		12	22	ns
Qg	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -4.5 \text{ A},$		10	14	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -4.5 V		2.2		nC
Q _{gd}	Gate-Drain Charge	1		1.5		nC
Drain-Se	ource Diode Characteristics a	and Maximum Ratings				
ls	Maximum Continuous Drain–Source I				-1.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -1.3 \text{ A} \text{(Note 2)}$		-0.73	-1.2	V

Notes

R_{0,N} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0,C} is guaranteed by design while R_{0,CA} is determined by the user's board design.



a) 78°C/W when mounted on a 1in² pad of 2 oz copper



b) 156°C/W when mounted on a minimum pad of 2 oz copper

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width $< 300\mu s$, Duty Cycle < 2.0%

Typical Characteristics

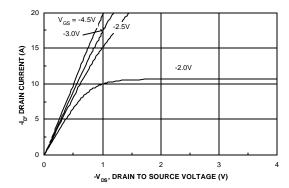


Figure 1. On-Region Characteristics.

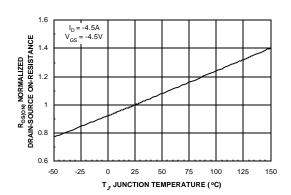


Figure 3. On-Resistance Variation with Temperature.

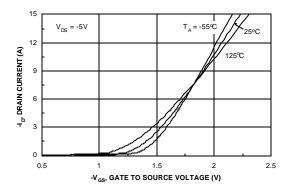


Figure 5. Transfer Characteristics.

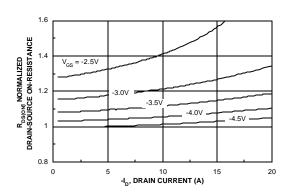


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

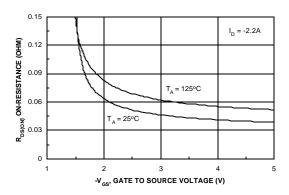


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

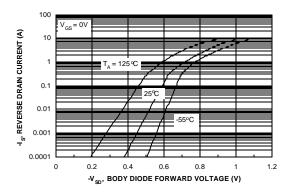
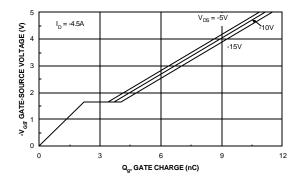


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



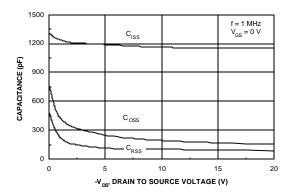
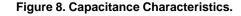
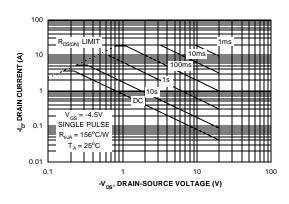


Figure 7. Gate Charge Characteristics.





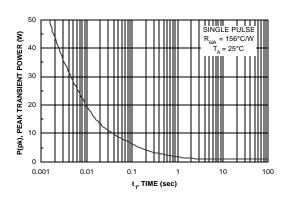


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

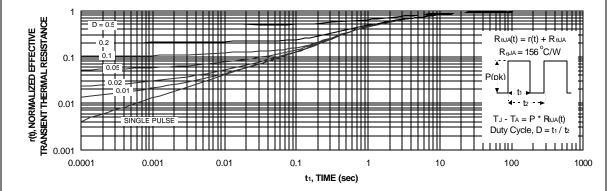


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b Transient thermal response will change depending on the circuit board design.

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